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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/713,117	11/17/2003	Woon-Kyung Lee	SEC.697D	9793	
75	7590 04/19/2005		EXAMINER		
VOLENTINE FRANCOS, PLLC			TRINH, MICHAEL MANH		
SUITE 150 12200 SUNRISE VALLEY DRIVE			ART UNIT	PAPER NUMBER	
RESTON, VA	20191		2822		
			DATE MAILED: 04/19/2009	DATE MAILED: 04/19/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
Office Action Summan	10/713,117	LEE ET AL.	(din)			
Office Action Summary	Examiner	Art Unit				
	Michael Trinh	2822				
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	correspondence ad	dress			
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	I36(a). In no event, however, may a reply be tin ly within the statutory minimum of thirty (30) day will apply and will expire StX (6) MONTHS from e, cause the application to become ABANDONE	nely filed s will be considered timely the mailing date of this co D (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 17 N	lovember 2003.					
	s action is non-final.					
3) Since this application is in condition for allowa closed in accordance with the practice under <i>t</i>	nce except for formal matters, pro		merits is			
Disposition of Claims						
4) ☐ Claim(s) 11-24 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 11-24 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or subject to restriction.	wn from consideration.					
Application Papers						
9) The specification is objected to by the Examine	er.					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the						
Replacement drawing sheet(s) including the correct						
11)☐ The oath or declaration is objected to by the Ex	xaminer. Note the attached Office	Action or form PT	O-152.			
Priority under 35 U.S.C. § 119						
a) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the prio application from the International Burea * See the attached detailed Office action for a list	ts have been received. Is have been received in Applicationity documents have been received u (PCT Rule 17.2(a)).	on No. <u>09/566,916</u> ed in this National				
Attachment(s)						
1) Notice of References Cited (PTO-892)	4) Interview Summary	(PTO-413)				
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date <u>11-17-03</u>. 	Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate 'atent Application (PTO	-152)			

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DETAILED ACTION

*** This office action is in response to filling of the application on November 17, 2003. Claims 1-10 were canceled. Claims 11-24 are current pending.

Claim Rejections - 35 USC § 112

- 1. Claims 11-17,19-20, and 21-24 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- ** Claim 11 is indefinite and incomplete, since it depends on canceled claim 1. Other dependent claims are rejected as depending on rejected indefinite base claim.
- ** Claim 21 (lines 13-14) is unclear for using of different terms for the same layer. It is suggested the term "a second silicon layer" (at lines 13-14 of claims 18 and 21) be amended as -- a second polysilicon layer--, since "the first and second polysilicon layers" is already mentioned at line 15, claim 21 (claims 23 and 24 also recite "polysilicon").
- ** Similarly, Claim 18 (lines 13-14) is unclear for using of different terms for the same layer. It is suggested the term "a second silicon layer" be amended as --a second polysilicon layer--, since "the first and second polysilicon layers" is already mentioned at line 15, claim 21.

Allowable Subject Matter

- 2. Claims 18, 21-24 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. 112, 2nd paragraph, as suggestion and set forth in this Office action.
- The following is a statement of reasons for the indication of allowable subject matter. The references including Hasegawa (5,891,780), Sheng (5,585,297), Chung (5,891,779), of record, alone or in combination, do not anticipatively disclose each and every aspect of the claimed method, or fairly make a prima facie obvious case of the claimed method, in combination with other processing claimed limitations as recited in base claims, the inclusion of, as in claim 21, forming a photoresist patterns on the first polysilicon layer formed on the gate insulation layer, which entirely cover a peripheral circuit region but are patterned in a cell array region to expose regions which are to become buried impurity regions; performing ion

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implantation using the photoresist patterns as a mask so as to form buried impurity regions near the surface of the semiconductor substrate, wherein the buried impurity regions are parallel, separated from each other by a predetermined interval and extend in the same direction; removing the photoresist patterns, and sequentially stacking a second polysilicon layer and a metal silicide layer on the first polysilicon layer; and sequentially etching the first and second polysilicon layers and the metal silicide layer so as to form word lines, wherein the word lines are parallel, separated from each other by a predetermined interval and extend in the perpendicular direction to the buried impurity diffusion region.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael M. Trinh whose telephone number is (571) 272-1847. The examiner can normally be reached on M-F: 8:30 Am to 5:00 Pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application should be directed to the receptionist whose telephone number is (703) 308-0956. Oacs-9

Michael Trinh Primary Examiner